

## IN THE CLAIMS

1. (Currently amended) A fuse bank of a semiconductor memory device comprising:

a first laser fuse which includes a first laser fusing region which is stripe-shaped and disposed in a first direction, a first connecting line ~~region~~ partially in the first laser fusing region, the first connection line ~~region~~ is disposed to be bent in a second direction, and a second connecting line ~~region~~ partially in the first laser fusing region, the second connecting line ~~region~~ is disposed to be bent in a third direction; and

a second laser fuse which includes a second laser fusing region which is stripe-shaped and disposed in the first direction, a third connecting line ~~region~~ partially in the second laser fusing region, the third connection line ~~region~~ is disposed to be bent in the second direction, and a fourth connecting line ~~region~~ partially in the second laser fusing region, the fourth connection line ~~region~~ is disposed to be bent in the third direction,

wherein the first laser fuse and the second laser fuse are disposed adjacently in the fuse bank with a space of a predetermined distance there between, the first laser fusing region and the second laser fusing region form a laser fusing region of the fuse bank, and

the first laser fuse and the second laser fuse are disposed on a plane, such that a lateral size of the fuse bank in the first direction is equal to a number of fuses in the fuse bank minus one multiplied by a pitch between the connecting lines, plus twice the width of the connecting lines, plus a length of the laser fusing region, and wherein the second direction is perpendicular to the first direction and opposite the third direction is directly proportional to a number of fuses times a pitch between the connecting line regions of the first and second laser.

2. (Original) The fuse bank of claim 1, wherein the laser fusing region has a parallelogram shape.

3. (Canceled)

4. (Canceled)

5. (Currently amended) A fuse bank of a semiconductor memory device comprising:

a first laser fuse group having multiple laser fuses disposed on a plane arranged in a first direction with a space of a predetermined distance there between; and

a second laser fuse group having multiple laser fuses disposed on the plane arranged in the first direction with a space of a predetermined distance there between, and

wherein each laser fuse in each laser fuse group each include a stripe-shaped laser fusing region disposed in the first direction, a first connecting line region partially in the first laser fusing region disposed to be bent in a second direction, and a second connecting line region disposed to be bent in a third direction, and that a lateral size of the fuse bank in the first direction is directly proportional to a number of fuses times a pitch between the connecting line regions of the laser fuses is equal to a number of fuses in the fuse bank minus one multiplied by a pitch between the connecting lines, plus twice the width of the connecting lines, plus a length of the laser fusing region, and wherein the second direction is perpendicular to the first direction and opposite the third direction.

6. (Original) The fuse bank of claim 5, wherein the laser fusing region has a parallelogram shape.

7. (Canceled)

8. (Canceled)

9. (Original) The fuse bank of claim 5, wherein the first laser fuse group and the second laser fuse group are disposed repeatedly.

10. (Currently amended) A fuse bank of a semiconductor memory device comprising:

a first laser fuse group having multiple laser fuses arranged in a first direction with a space of a predetermined distance there between; and

a second laser fuse group having multiple laser fuses arranged in the first direction with a space of a predetermined distance there between,

wherein each laser fuse in each laser fuse group includes a stripe-shaped laser fusing region disposed in the first direction, a first connecting line region partially in the first laser fusing region disposed to be bent in a second direction, and a second connecting line region partially in the first laser fusing region disposed to be bent in a third direction,

the first laser fuse group and the second laser fuse group are disposed adjacently,

the first laser fuse group and the second laser fuse group are disposed to be symmetrical about the direction perpendicular to the first direction, and

the first laser fuse group and the second laser fuse group are disposed on a plane, such that a lateral size of the fuse bank in the first direction is directly proportional to a number of fuses times a pitch between the connecting line regions of the laser fuses is equal to a number of fuses in the fuse bank minus one multiplied by a pitch between the connecting lines, plus twice the width of the connecting lines, plus a length of the laser fusing region, and wherein the second direction is perpendicular to the first direction and opposite the third direction.

11. (Original) The fuse bank of claim 10, wherein the laser fusing region has a parallelogram shape.

12. (Canceled)

13. (Canceled)

14. (Original) The fuse bank of claim 10, wherein the first laser fuse group and the second laser fuse group are disposed repeatedly.

15. (Currently amended) A fuse bank, comprising:

a fuse region formed from a first fuse region and a second fuse region, the first and second fuse regions arranged parallel to each other in a first direction in the bank, each with a first end and a second end; and

connecting lines connected to each of the first and second fuse regions, such that each of the first and second fuse regions has a connecting line on each end, wherein connecting lines on the first end are perpendicular to the first and second fuse regions and parallel to each other in a second direction and connecting lines on the second end are perpendicular to the first and second fuse regions and parallel to each other in a third direction, and that a lateral size of the fuse bank in the first direction is ~~directly proportional to a number of fuses times a pitch between the connecting line regions the laser fuses~~ is equal to a number of fuses in the fuse bank minus one multiplied by a pitch between the connecting lines, plus twice the width of the connecting lines, plus a length of the laser fusing region, and wherein the second direction is perpendicular to the first direction and opposite the third direction.

16. (Previously presented) The fuse bank of claim 15, the first and second fuse regions being offset from each other by a predetermined distance.

17. (Previously presented) The fuse bank of claim 15, connecting lines at each end of the fuse region being offset from each other by a predetermined distance.

18. (Canceled)

19. (Canceled)

20. (Canceled)